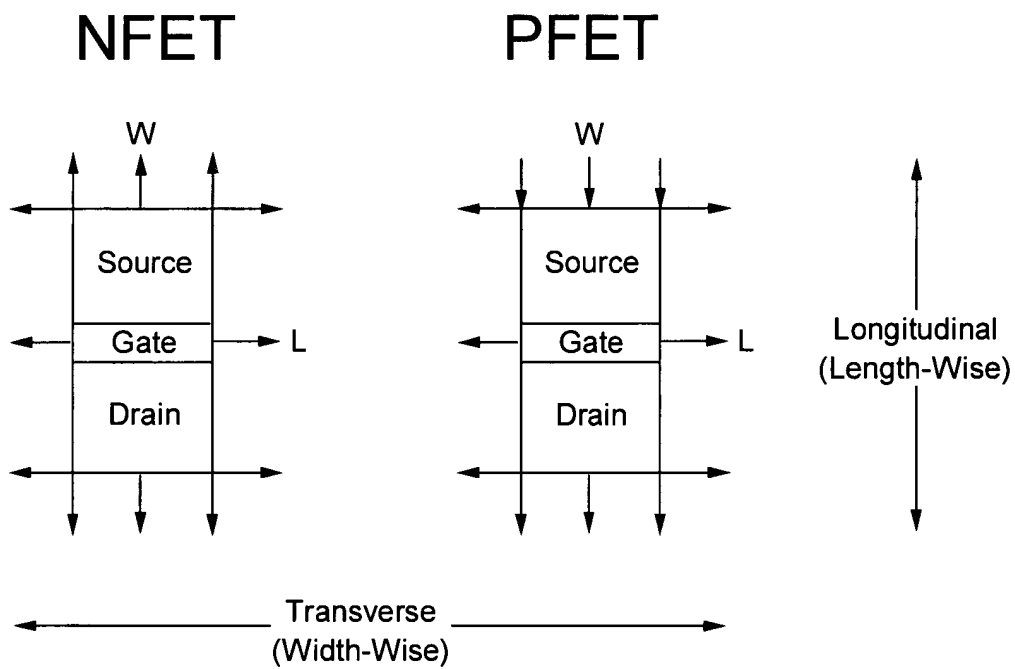




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FIG. 1



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FIG. 2A

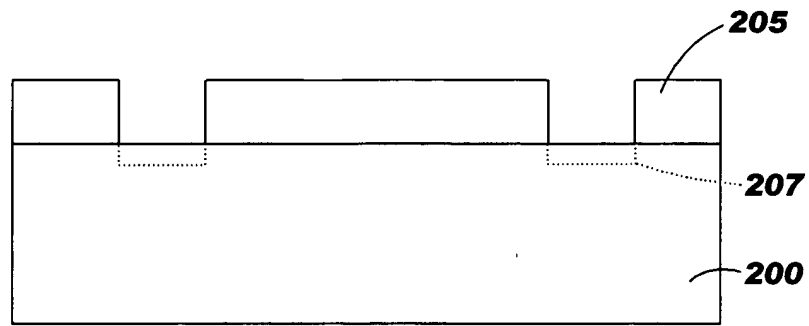


FIG. 2B

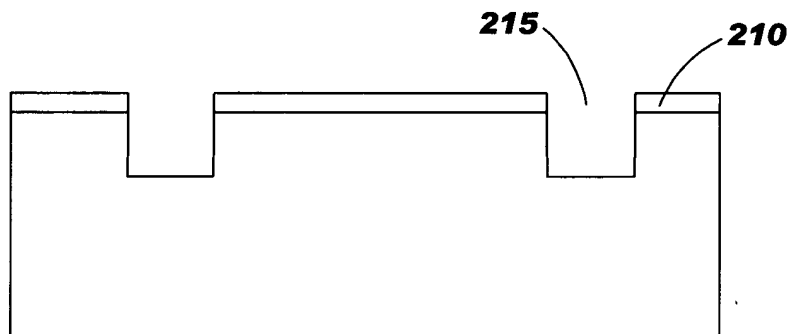
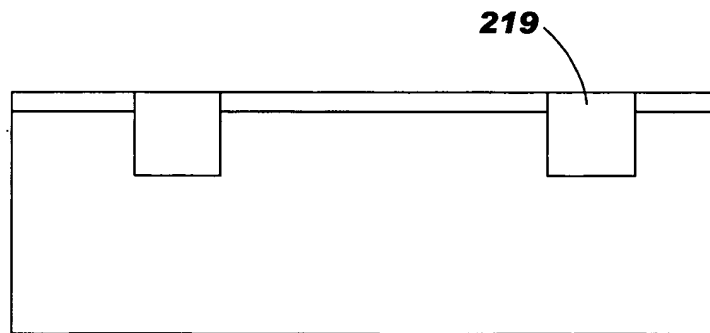


FIG. 2C



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FIG. 2D

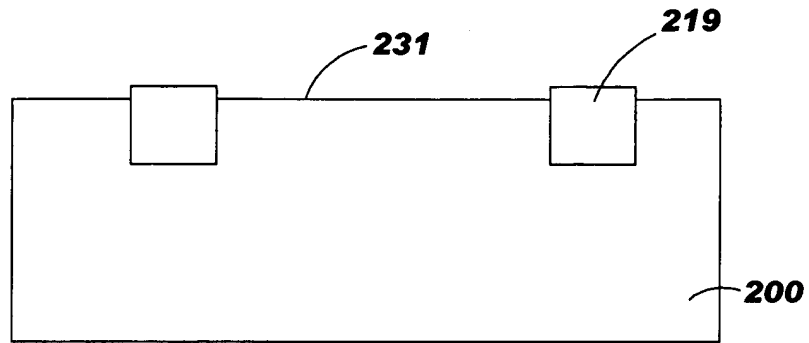


FIG. 2E

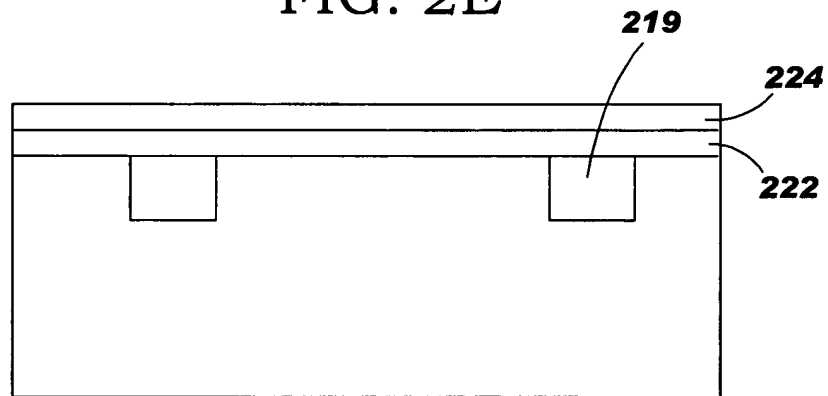
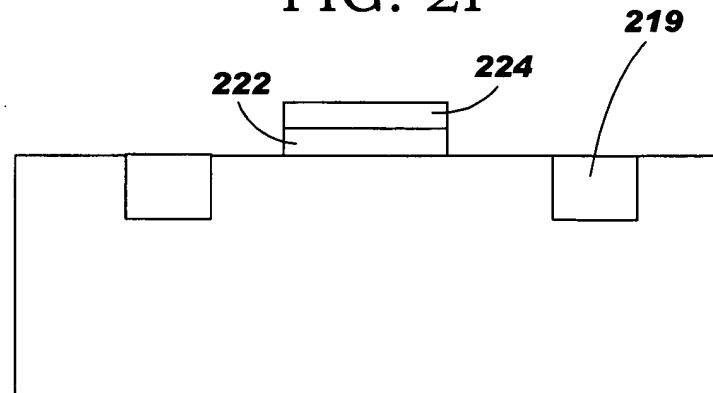


FIG. 2F



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FIG. 2G

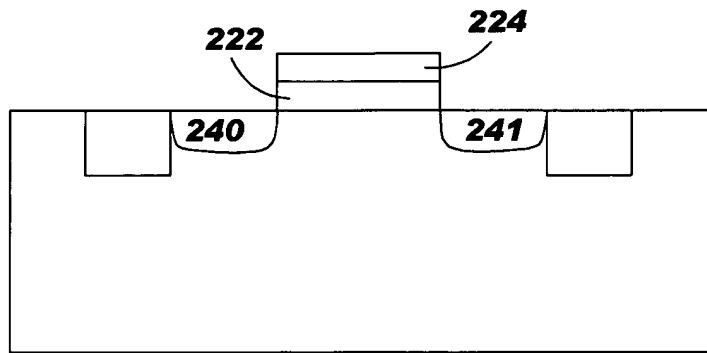


FIG. 2H

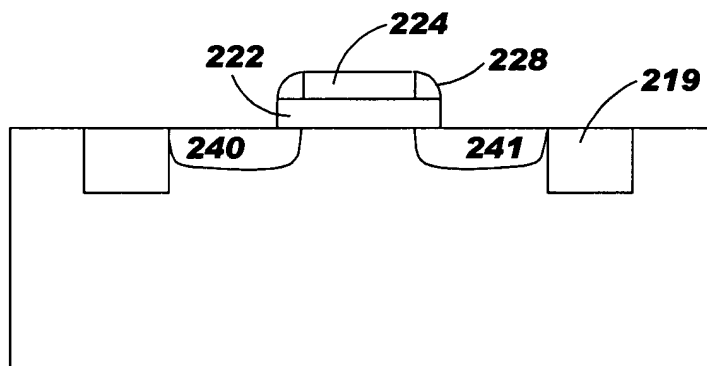
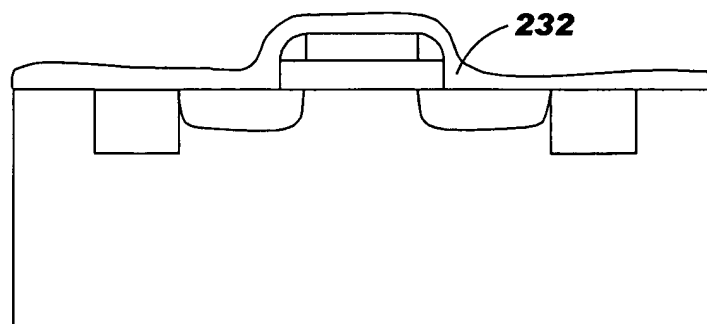


FIG. 2I



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FIG. 2J

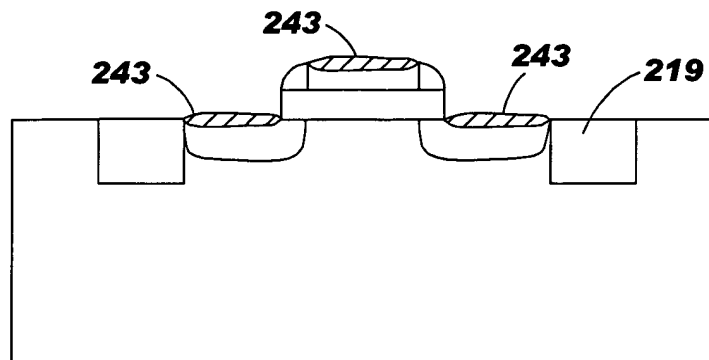


FIG. 2K

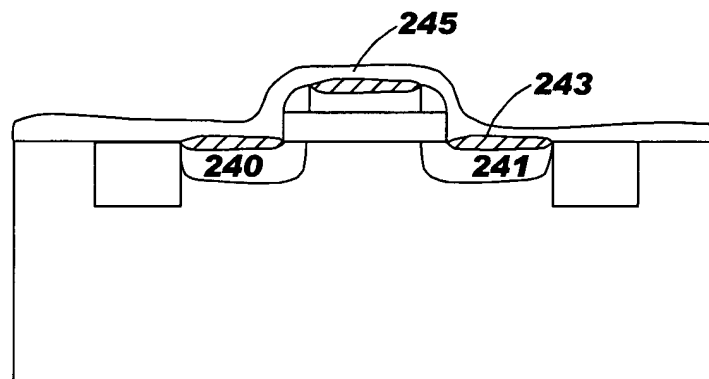
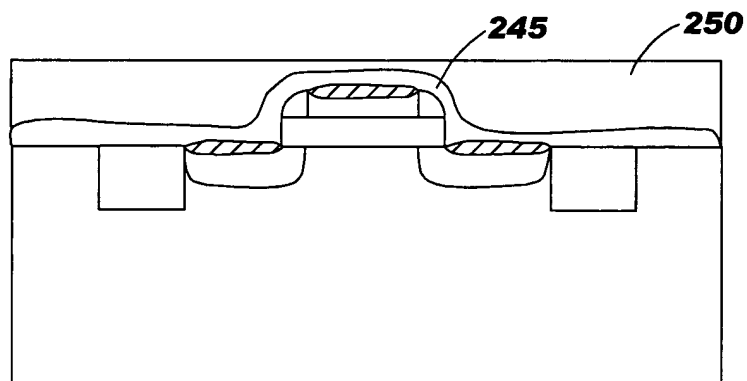


FIG. 2L



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FIG. 3

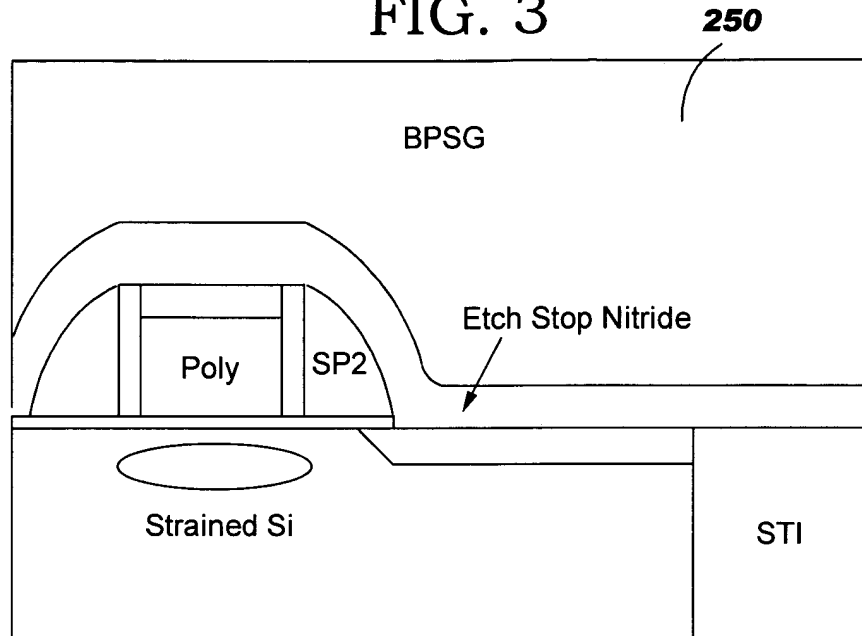
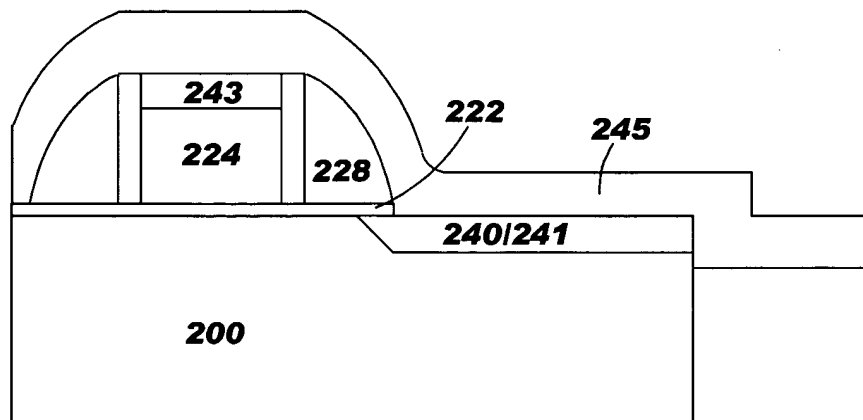


FIG. 4



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FIG. 5

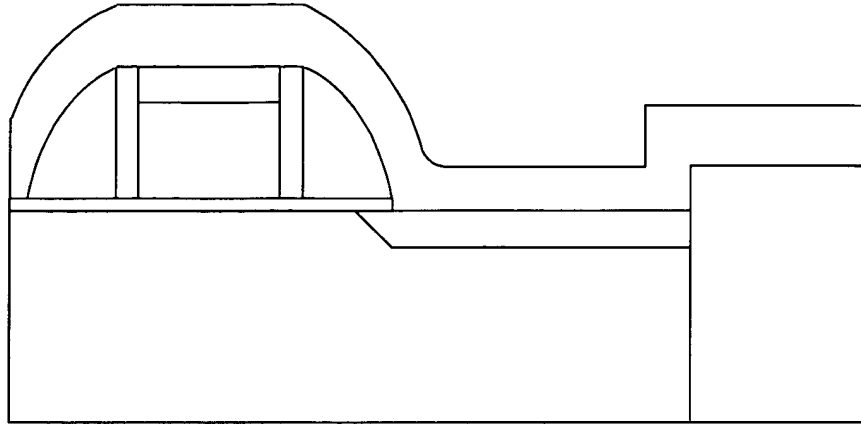
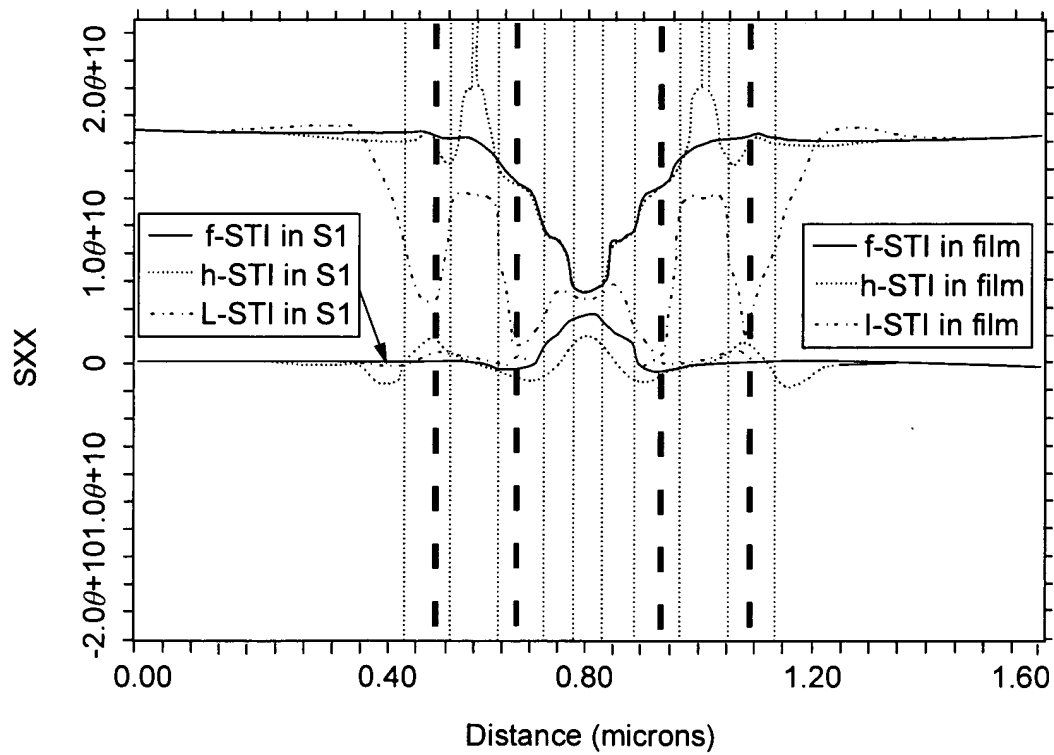


FIG. 6

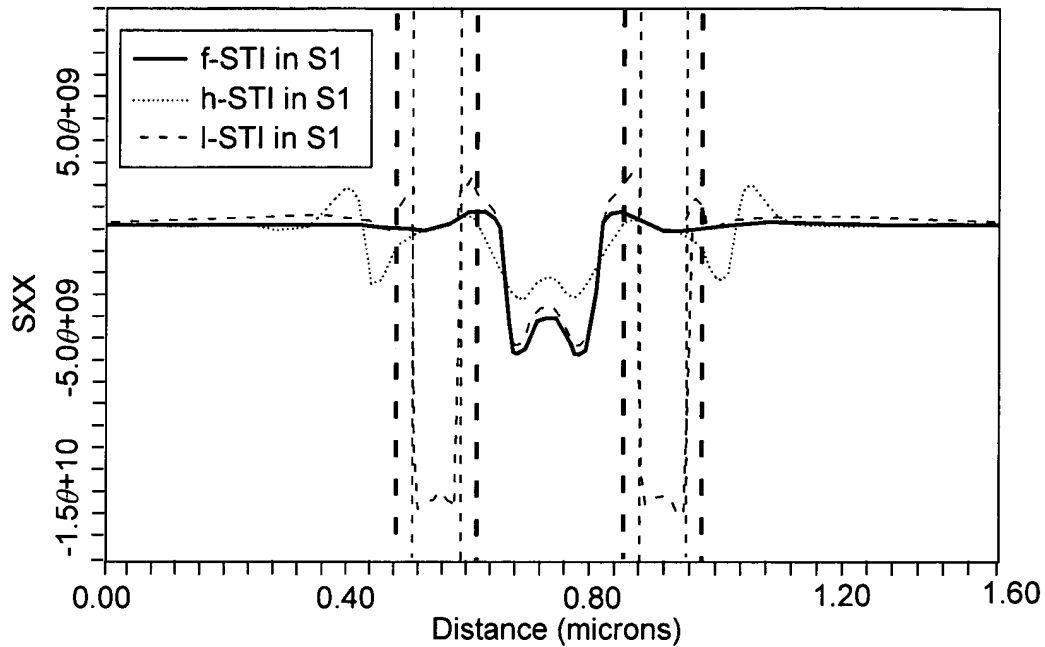
Stress Sxx vs. hight of STI-oxide
In Si cut at $y = +0.01\mu\text{m}$ and In film $y = -0.01\mu\text{m}$
Pressure (dynes/cm²)



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Stress Sxx vs. height of STI-oxide
in Si cut at $y=+0.01\mu\text{m}$
Pressure (dynes/cm²)

FIG. 7



Stress Sxx vs. height of STI-oxide w/large PC-STI distance
in Si cut at $y=0.01\mu\text{m}$ and in film $y=0.01\mu\text{m}$
Pressure (dynes/cm²)

FIG. 8

